TOSHIBA Transistor Silicon NPN Epitaxial Type (PCT Process)

# HN1C01FU

Audio Frequency General Purpose Amplifier Applications

- Small package (Dual type)
- High voltage and high current

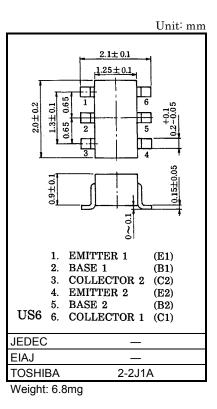
: VCEO = 50V, IC = 150mA (max)

- High  $h_{FE}$ :  $h_{FE} = 120 \sim 400$
- Excellent hFE linearity

:  $h_{FE}$  (I<sub>C</sub> = 0.1mA) /  $h_{FE}$  (I<sub>C</sub> = 2mA) = 0.95 (typ.)

#### Maximum Ratings (Ta = 25°C) (Q1, Q2 Common)

Characteristic	Symbol	Rating	Unit	
Collector-base voltage	V <sub>CBO</sub>	60	V	
Collector-emitter voltage	V <sub>CEO</sub>	50	V	
Emitter-base voltage	V <sub>EBO</sub>	5	V	
Collector current	۱ <sub>C</sub>	150	mA	
Base current	Ι <sub>Β</sub>	30	mA	
Collector power dissipation	P <sub>C</sub> *	200	mW	
Junction temperature	Tj	125	°C	
Storage temperature range	T <sub>stg</sub>	-55~125	°C	



\* Total rating

### Electrical Characteristics (Ta = 25°C) (Q1,Q2 Common)

Characteristic	Symbol	Test Circuit	Test Condition	Min	Тур.	Max	Unit
Collector cut-off current	I <sub>CBO</sub>	_	$V_{CB} = 60V, I_E = 0$	_	_	0.1	μΑ
Emitter cut-off current	I <sub>EBO</sub>	—	V <sub>EB</sub> = 5V, I <sub>C</sub> = 0	-	-	0.1	μA
DC current gain	h <sub>FE (Note)</sub>	—	$V_{CE}$ = 6V, I <sub>C</sub> = 2mA	120	_	400	
Collector-emitter saturation voltage	V <sub>CE (sat)</sub>	_	I <sub>C</sub> = 100mA, I <sub>B</sub> = 10mA	-	0.1	0.25	V
Transition frequency	f <sub>T</sub>	_	V <sub>CE</sub> = 10V, I <sub>C</sub> = 1mA	80	_	_	MHz
Collector output capacitance	C <sub>ob</sub>	—	V <sub>CB</sub> = 10V, I <sub>E</sub> = 0, f = 1MHz	_	2	3.5	pF

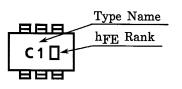
Note: hfe Classification

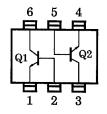
Y (Y): 120~240, GR (G): 200~400

( ) Marking Symbol

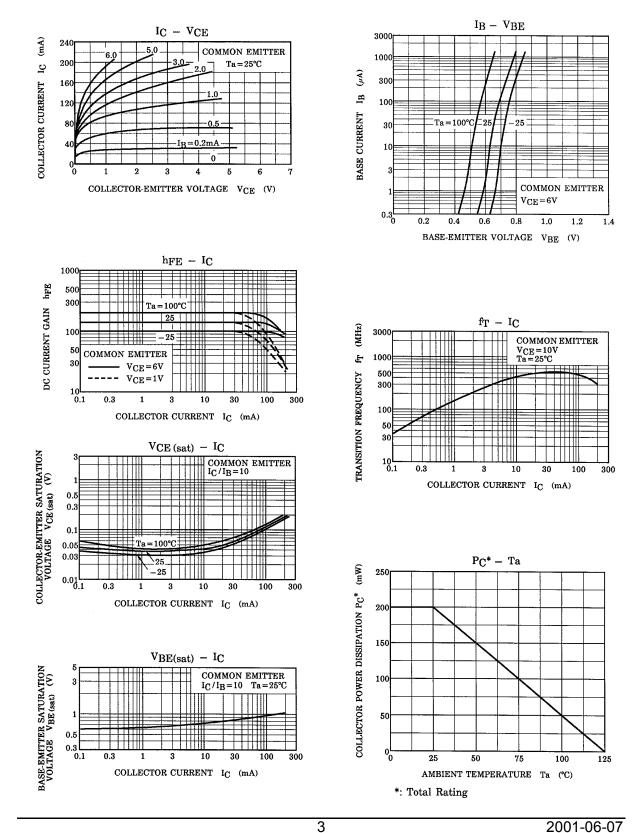
## Marking

## Equivalent Circuit (Top View)





(Q1,Q2 Common)



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